



Features

Environments

robust end application

PPAP Capable (Note 4)

Mechanical Data

Case: TO263AB

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 $\label{eq:low-RDS} \begin{array}{l} \mbox{Low R}_{DS(ON)} - \mbox{Minimizes Power Losses} \\ \mbox{Low Q}_g - \mbox{Minimizes Switching Losses} \end{array}$

Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020

Weight: 1.7 grams (Approximate)

Solderable per MIL-STD-202, Method 208 @3

Lead-Free Finish; RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

DMTH4004SCTBQ

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Rated to +175°C - Ideal for High Ambient Temperature

100% Unclamped inductive switching ensures more reliable and

Case Material: Molded Plastic, "Green" Molding Compound; UL

Terminal Finish - Matte Tin Annealed over Copper Leadframe.

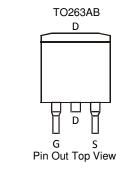
Product Summary

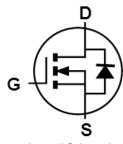
BV _{DSS}	R _{DS(ON)} Max	Q _g Тур	I _D T _C = +25°C (Note 10)
40V	3mΩ @ V _{GS} = 10V	68.6nC	100A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters





Internal Schematic

Ordering Information (Note 5)

Top View

Part Number	Case	Packaging
DMTH4004SCTBQ-13	TO263AB	800/Tape & Reel

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

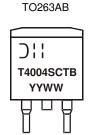
4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to

http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



T4004SCTB = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 14 = 2014) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 7)	T _C = +25°C (Note 10)	ID	100	А
	$T_{\rm C} = +100^{\circ}{\rm C}$	D	100	
Maximum Continuous Body Diode Forward Current		ls	100	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	200	A	
Avalanche Current, L=0.2mH	IAS	45	A	
Avalanche Energy, L=0.2mH		Eas	200	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	PD	4.7	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta JA}$	32	°C/W
Total Power Dissipation (Note 7)	$T_{\rm C} = +25^{\circ}{\rm C}$	PD	136	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			_				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	—		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2.5	3	mΩ	$V_{GS} = 10V, I_D = 100A$	
Diode Forward Voltage	V _{SD}	—	—	1.3	V	$V_{GS} = 0V, I_{S} = 100A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	4,305	_		$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	1,441	_	pF		
Reverse Transfer Capacitance	Crss	_	102	_			
Gate Resistance	R _G	_	0.77	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	—	68.6	_		$\label{eq:VDD} \begin{split} V_{DD} &= 20V, \ I_D = 90A, \\ V_{GS} &= 10V \end{split}$	
Gate-Source Charge	Q _{gs}	—	16.8	_	nC		
Gate-Drain Charge	Q _{gd}	_	14.2	_			
Turn-On Delay Time	t _{D(ON)}	_	9.5	_		$\label{eq:VDD} \begin{split} V_{DD} &= 20V, \ V_{GS} = 10V, \\ I_D &= 90A, \ R_G = 3.5\Omega \end{split}$	
Turn-On Rise Time	t _R	_	6.7				
Turn-Off Delay Time	t _{D(OFF)}	—	26.4		ns		
Turn-Off Fall Time	tF	—	8.1				
Reverse Recovery Time	t _{RR}	—	52.4		ns		
Reverse Recovery Charge	Q _{RR}	_	78.2		nC	I _F = 50A, di/dt = 100A/μs	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

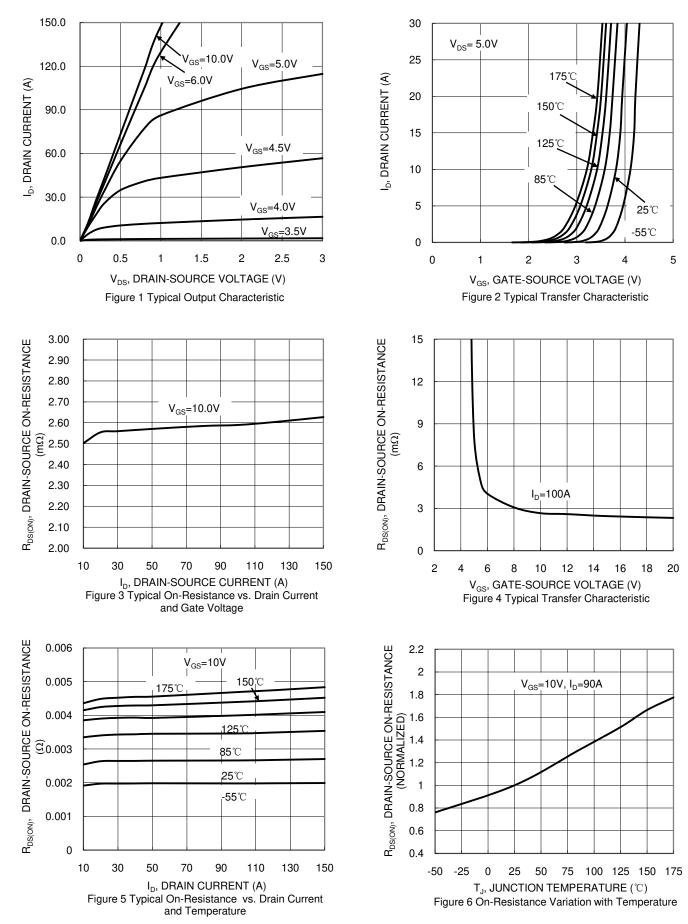
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

10. Package limited.



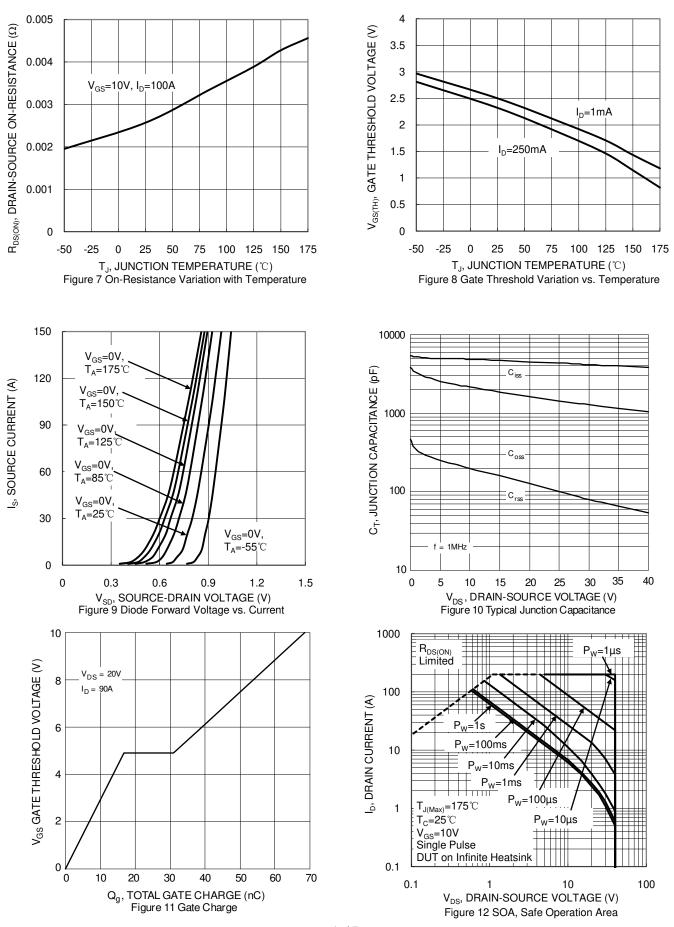
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DMTH4004SCTBQ Document number: DS37796 Rev. 2 - 2 3 of 7 www.diodes.com

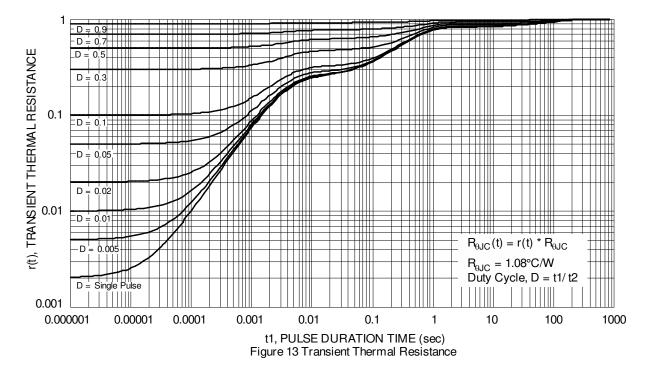


DMTH4004SCTBQ



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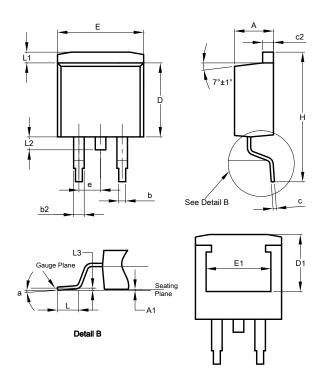




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TO263AB (D2PAK)

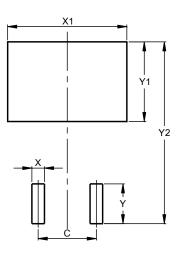


то	TO263AB (D2PAK)					
Dim	Min	Max	Тур			
Α	4.07	4.82	-			
A1	0.00	0.25	-			
b	0.51	0.99	-			
b2	1.15	1.77	-			
С	0.356	0.73	-			
c2	1.143	1.65	-			
D	8.39	9.65	-			
D1	6.55	6.95	-			
е		2.54 TYP				
E	9.66	10.66	-			
E1	6.23	8.23	-			
Н	14.61	15.87	-			
L	1.78	2.79	-			
L1	-	1.67	-			
L2	-	1.77	-			
L3	-	-	0.254			
а	0°	8°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO263AB (D2PAK)



Dimensions	Value (in mm)			
С	5.08			
Х	1.10			
X1	10.41			
Y	3.50			
Y1	7.01			
Y2	15.99			



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